

1200V SiC MOSFET

V_{DS}	1200 V
$R_{DS,on}$	37 m Ω
I_D (TC=25°C)	63 A
$T_{j,max}$	175°C

Features

- High speed switching
- Reliable body diode
- All parts tested to greater than 1,400V
- Avalanche tested to 400mJ*

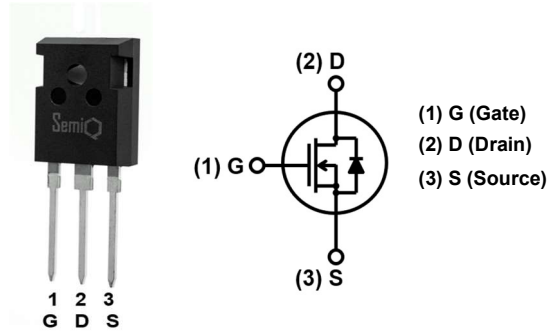
Benefits

- Lower capacitance
- Higher system efficiency
- Easy to parallel

Applications

- Solar Inverters
- Switch mode power supplies, UPS
- Induction heating and welding
- EV charging stations
- High voltage DC/DC converters
- Motor drives

Package



Part #	Package	Marking
GP2T040A120U	TO-247-3L	2T040A120



Maximum Ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit
Drain-Source Voltage	V_{rated}	$V_{GS}=0V, I_{DS}=1\mu A$	1200	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}, T_j=175^\circ\text{C}$	63	A
		$T_C=100^\circ\text{C}, T_j=175^\circ\text{C}$	47	
Pulsed Drain Current	$I_{D,pulse}^*$	$T_C=25^\circ\text{C}$	160	
Gate Source Voltage	V_{GSmax}		-10/25	V
	V_{GSop}	Recommended operational	-5/20	
Power Dissipation	P_{tot}	$T_C=25^\circ\text{C}$	322	W
Operating & Storage Temperature	$T_j, T_{storage}$	Continuous	-55...175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=1.0mH, I_{AS}=28.3A, V=50V$	400	mJ

Thermal Characteristics

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal Resistance, Junction to Case	R_{thJC}		-	0.38	0.47	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	R_{thJA}		-	-	40.0	

* Pulse width is limited by $T_{j,max}$

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Static Electrical Characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-Source Breakdown Voltage	BV_{DSS}	$I_{DS}=1\text{mA}$	1200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200\text{V}, V_{GS}=0\text{V}$	-	0.1	1.0	μA
		$V_{DS}=1200\text{V}, V_{GS}=0\text{V}, T_j=175^\circ\text{C}$	-	1	-	
Gate-Source Leakage Current	I_{GSS+}	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	<+10	100	nA
	I_{GSS-}	$V_{GS}=-5\text{V}, V_{DS}=0\text{V}$	-	>-10	-100	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_{DS}=10\text{mA}$	2	2.4	4	V
		$V_{GS}=V_{DS}, I_{DS}=10\text{mA}, T_j=125^\circ\text{C}$	-	1.8	-	
		$V_{GS}=V_{DS}, I_{DS}=10\text{mA}, T_j=175^\circ\text{C}$	-	1.6	-	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=20\text{V}, I_{DS}=40\text{A}$	-	37	52	m Ω
		$V_{GS}=20\text{V}, I_{DS}=20\text{A}$	-	35	45	
		$V_{GS}=20\text{V}, I_{DS}=40\text{A}, T_j=125^\circ\text{C}$	-	56	-	
		$V_{GS}=20\text{V}, I_{DS}=40\text{A}, T_j=175^\circ\text{C}$	-	73	-	
Transconductance	g_{fs}	$V_{DS}=20\text{V}, I_{DS}=40\text{A}$	-	16	-	S
Gate Input Resistance	R_G	$f=1\text{MHz}, V_{AC}=25\text{mV}, \text{D-S Short}$	-	1.9	-	Ω

AC Electrical Characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=1000\text{V}, f=200\text{kHz}, V_{AC}=25\text{mV}$	-	3192	-	pF
Output Capacitance	C_{OSS}		-	132	-	
Reverse Transfer Capacitance	C_{RSS}		-	7	-	
Coss Stored Energy	E_{OSS}		-	77	-	
Turn-On Switching Energy	E_{ON}	$V_{DD}=800\text{V}, I_{DS}=40\text{A}, R_{G(ext)}=2.5,$	-	1087	-	μJ
Turn-Off Switching Energy	E_{OFF}	$V_{GS}=-5/+20\text{V}, L=273\mu\text{H},$	-	86	-	
Total Switching Energy	E_{TOT}	$\text{FWD}=\text{GP2T040A120U}$	-	1173	-	
Turn-On Switching Energy	E_{ON}	$V_{DD}=800\text{V}, I_{DS}=40\text{A}, R_{G(ext)}=2.5,$	-	888	-	μJ
Turn-Off Switching Energy	E_{OFF}	$V_{GS}=-5/+20\text{V}, L=273\mu\text{H},$	-	94	-	
Total Switching Energy	E_{TOT}	$\text{FWD}=\text{GP3D020A120A}$	-	982	-	
Turn-On Delay Time	$t_{D(on)}$	$V_{DD}=800\text{V}, I_{DS}=40\text{A},$	-	15	-	ns
Rise Time	t_R	$R_{G(ext)}=2.5, V_{GS}=-5/+20\text{V},$	-	14	-	
Turn-Off Delay Time	$t_{D(off)}$	$L=273\mu\text{H},$	-	22	-	
Fall Time	t_F	$\text{FWD}=\text{GP2T040A120U}$	-	14	-	
Total Gate Charge	Q_G	$V_{DD}=800\text{V}, I_{DS}=40\text{A}, V_{GS}=-5/+20\text{V}$	-	118	-	nC
Gate to Source Charge	Q_{GS}		-	53	-	
Gate to Drain Charge	Q_{GD}		-	10	-	

Body Diode Characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Max Continuous Diode Fwd Current	I_S	$V_{GS}=-5\text{V}, T_C=25^\circ\text{C}$	-	-	74	A
Diode Forward Voltage	V_{SD}	$V_{GS}=-5\text{V}, I_{SD}=20\text{A}$	-	3.8	-	V
Reverse Recovery Time	t_{RR}	$I_{SD}=40\text{A}, V_R=800\text{V}, V_{GS}=-5\text{V}, di_F/dt=3.2\text{A/ns}$	-	28	-	ns
Reverse Recovery Charge	Q_{RR}		-	284	-	nC
Peak Reverse Recovery Current	I_{RRM}		-	18	-	A

Typical Performance

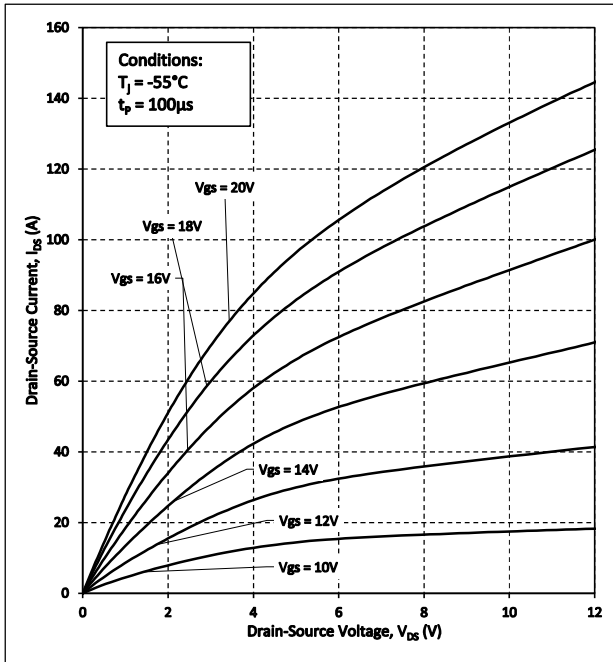


Figure 1. Output Characteristics $T_j = -55^\circ\text{C}$

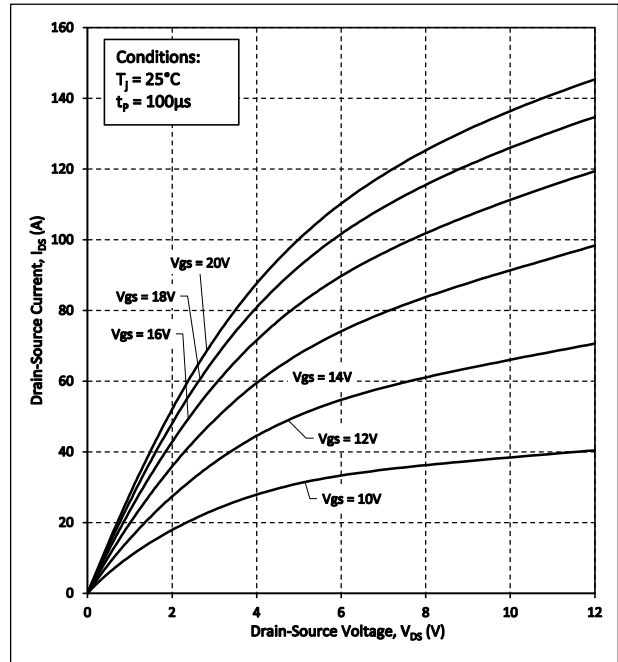


Figure 2. Output Characteristics $T_j = 25^\circ\text{C}$

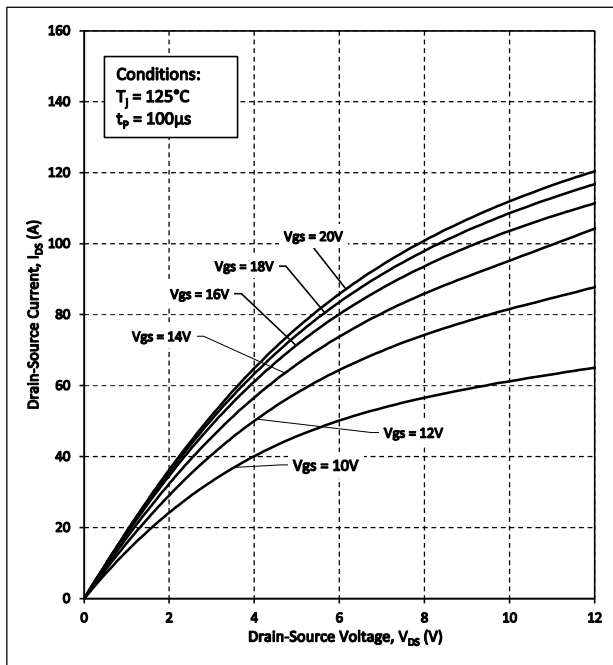


Figure 3. Output Characteristics $T_j = 125^\circ\text{C}$

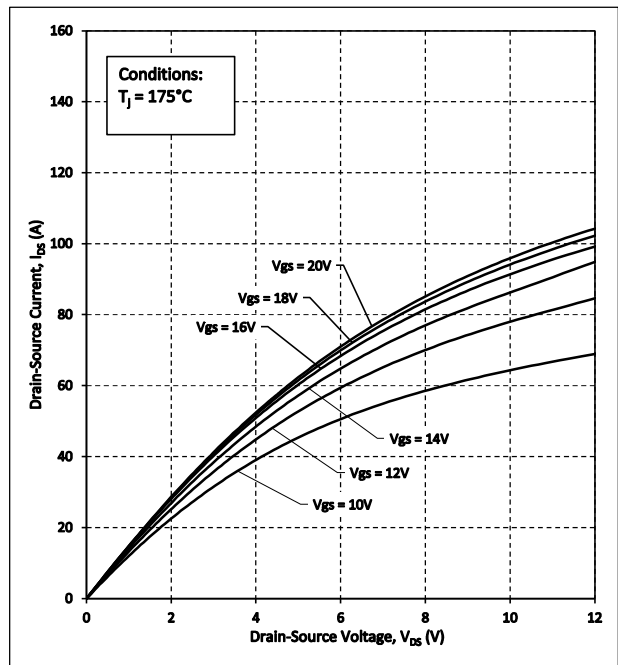


Figure 4. Output Characteristics $T_j = 175^\circ\text{C}$

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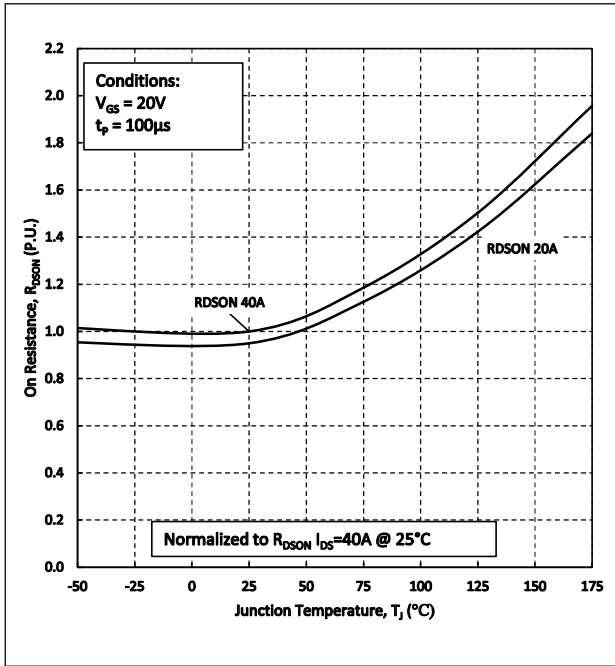


Figure 5. Normalized On-Resistance vs. Temperature

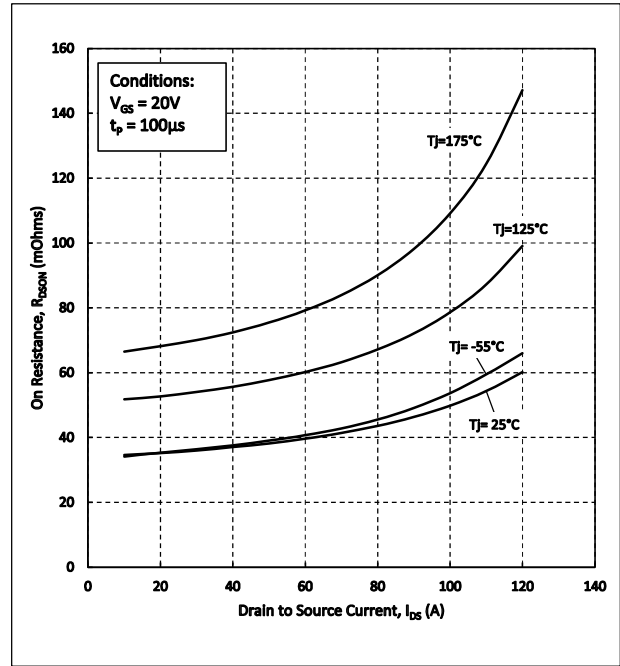


Figure 6. On-Resistance vs. Drain Current For Various Temperature

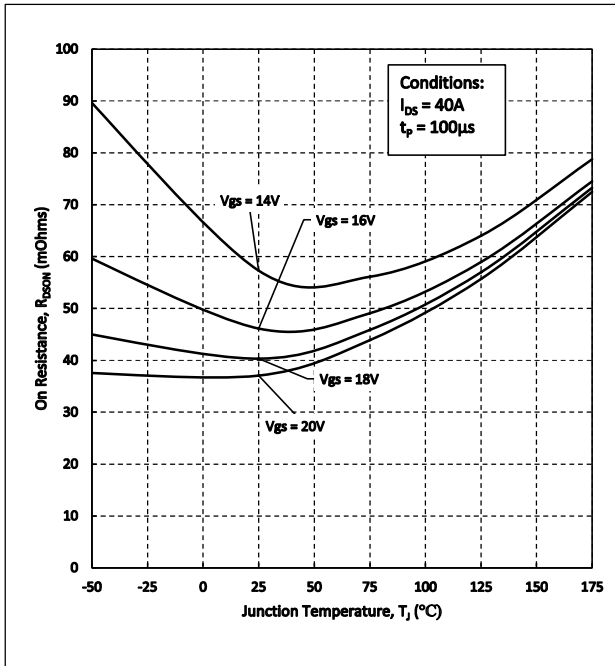


Figure 7. On-Resistance vs. Temperature For Various Gate Voltages

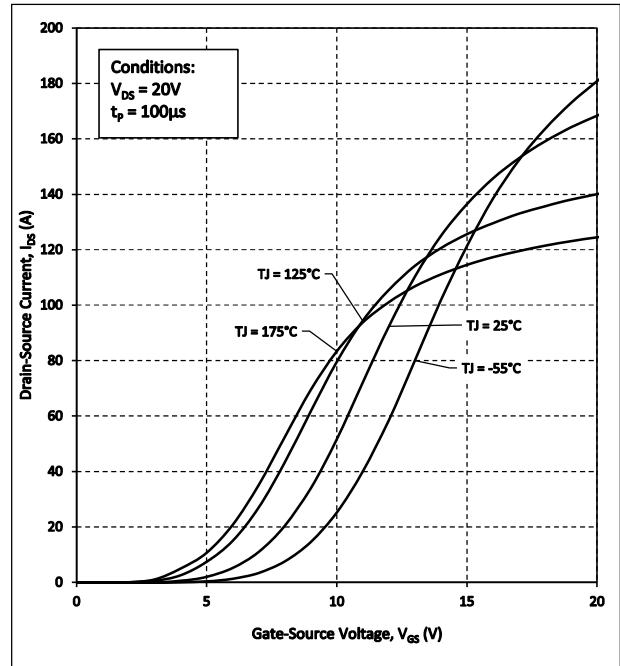


Figure 8. Transfer Characteristic for Various Junction Temperatures

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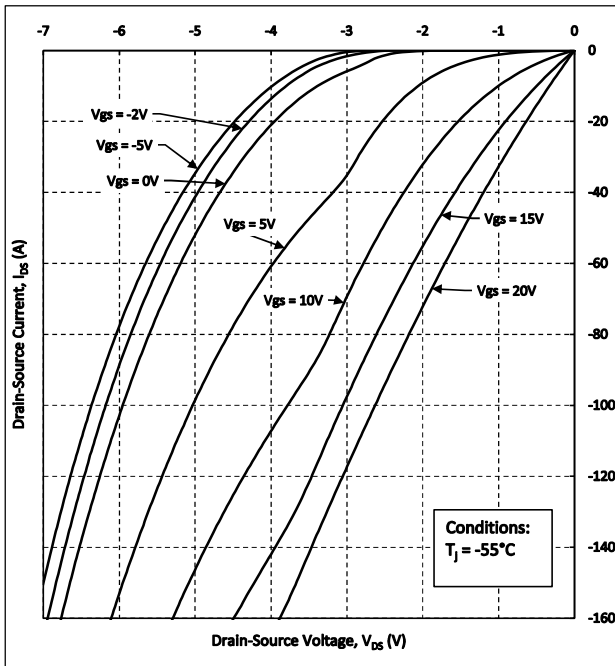


Figure 9. Body Diode Characteristics at $T_j = -55^\circ\text{C}$

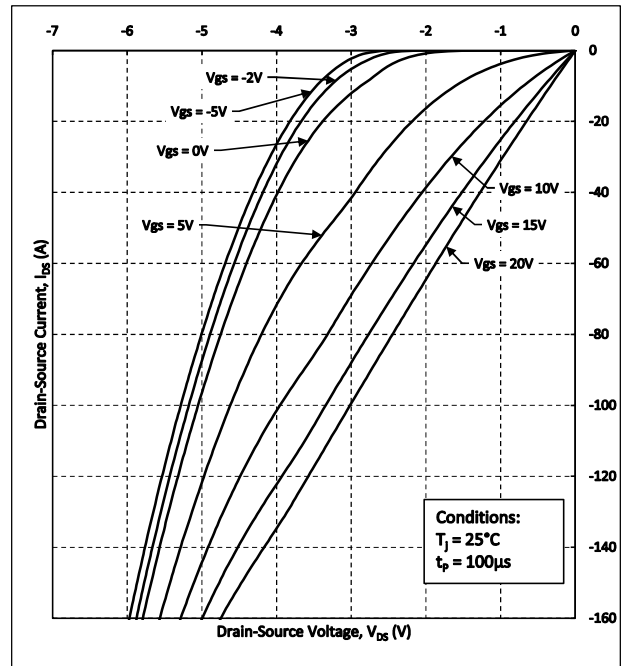


Figure 10. Body Diode Characteristics at $T_j = 25^\circ\text{C}$

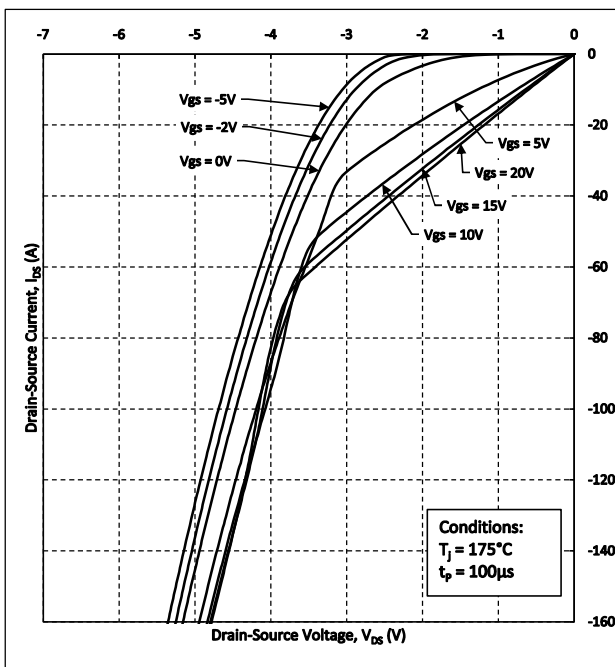


Figure 11. Body Diode Characteristics at $T_j = 175^\circ\text{C}$

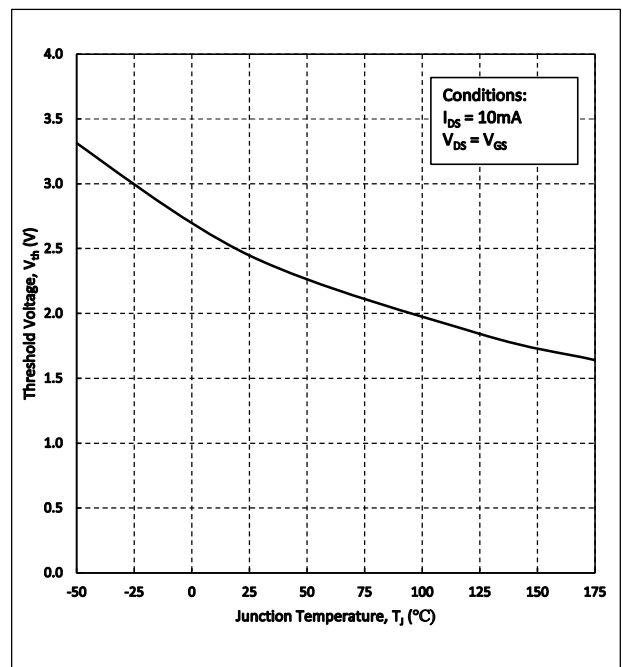


Figure 12. Threshold Voltage vs. Temperature

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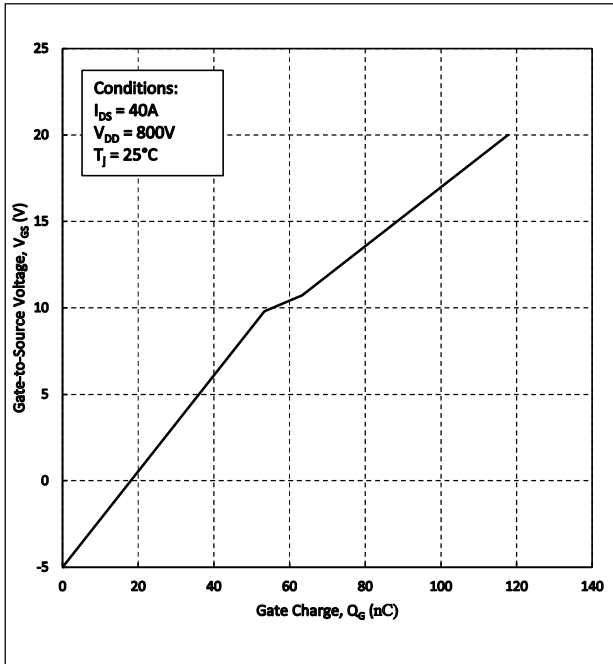


Figure 13. Gate Charge Characteristics

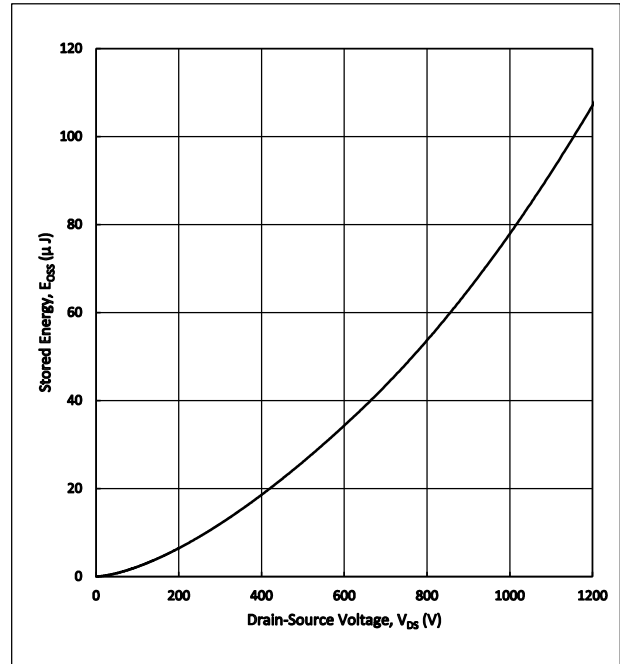


Figure 14. Output Capacitor Stored Energy

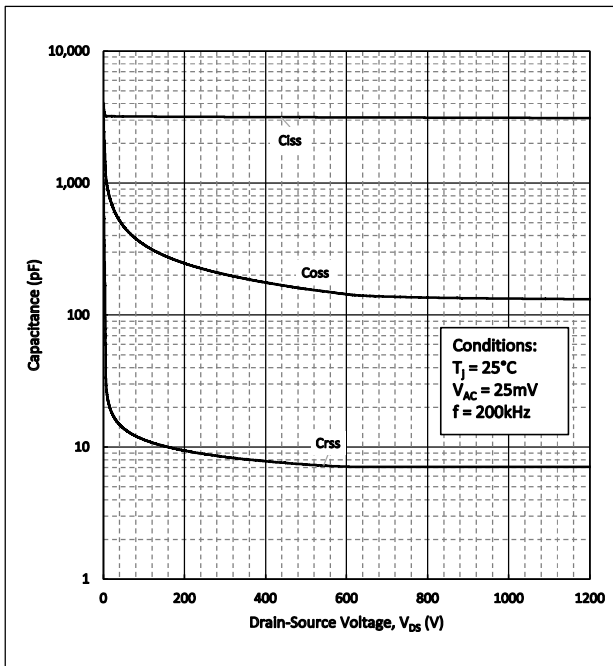


Figure 15. Capacitance vs Drain-Source Voltage

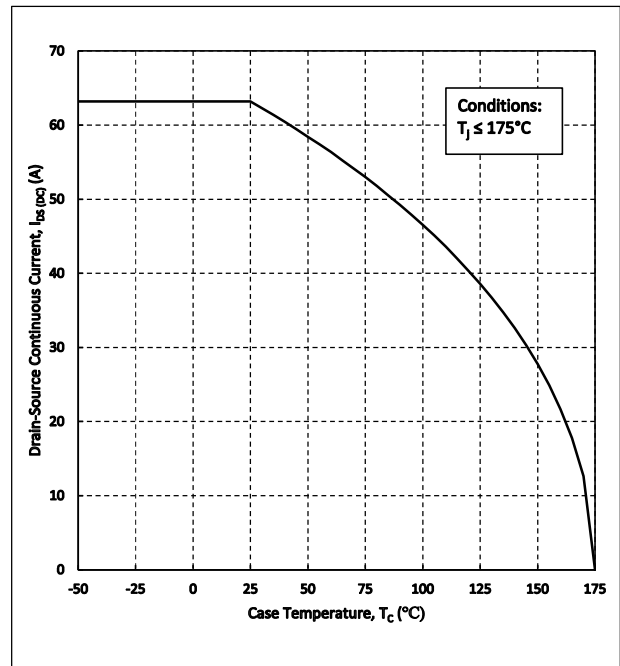


Figure 16. Continuous Drain Current Derating vs. Case Temperature

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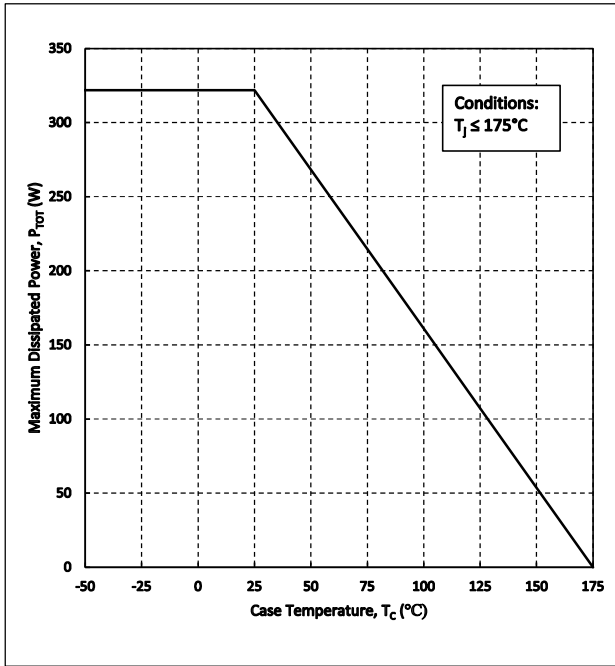


Figure 17. Maximum Power Dissipation Derating vs Case Temperature

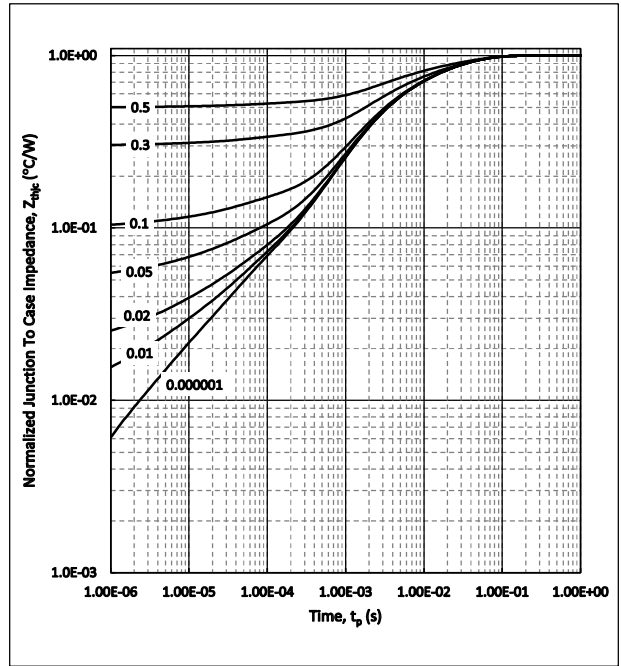


Figure 18. Transient Thermal impedance (Junction to Case)

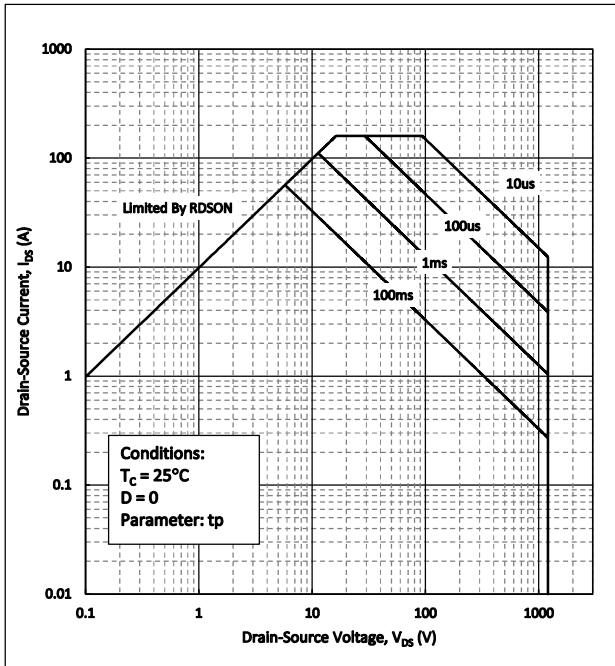


Figure 19. Safe Operating Area

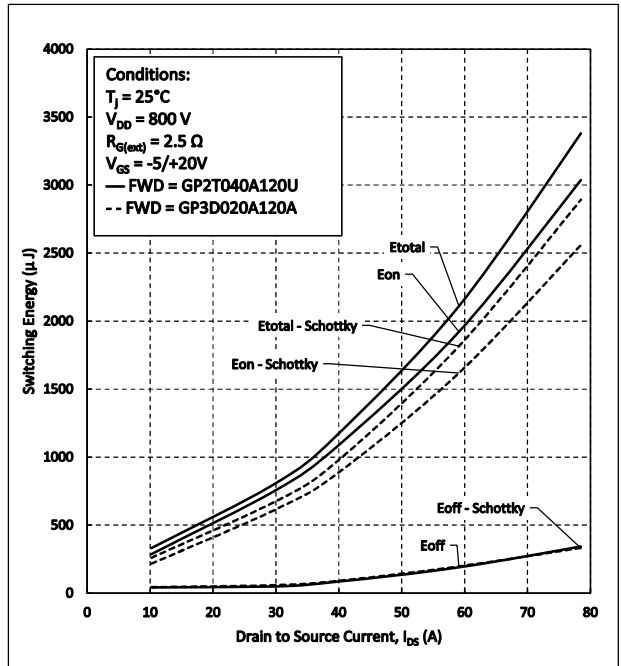


Figure 20. Clamped Inductive Switching Energy vs. Drain Current

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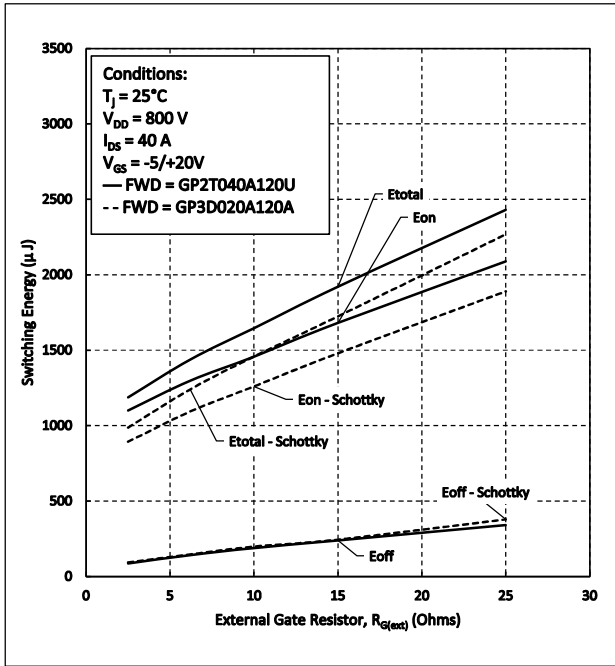


Figure 21. Clamped Inductive Switching Energy vs. $R_{G(\text{ext})}$

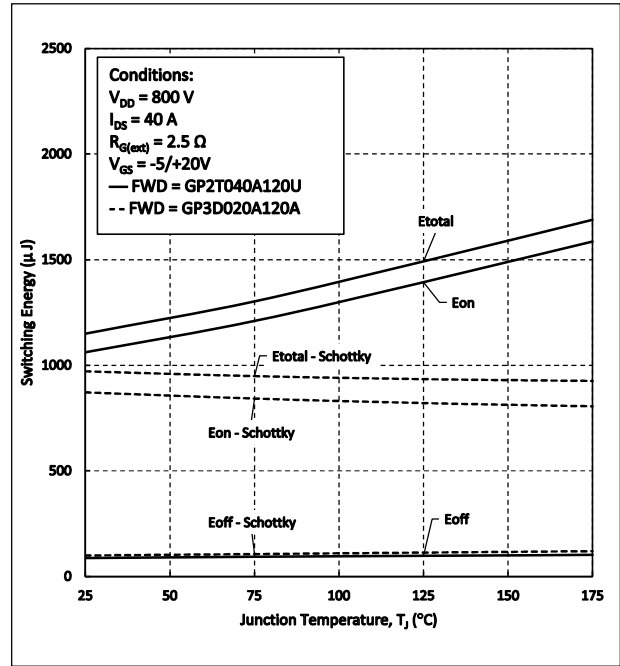


Figure 22. Clamped Inductive Switching Energy vs. Temperature

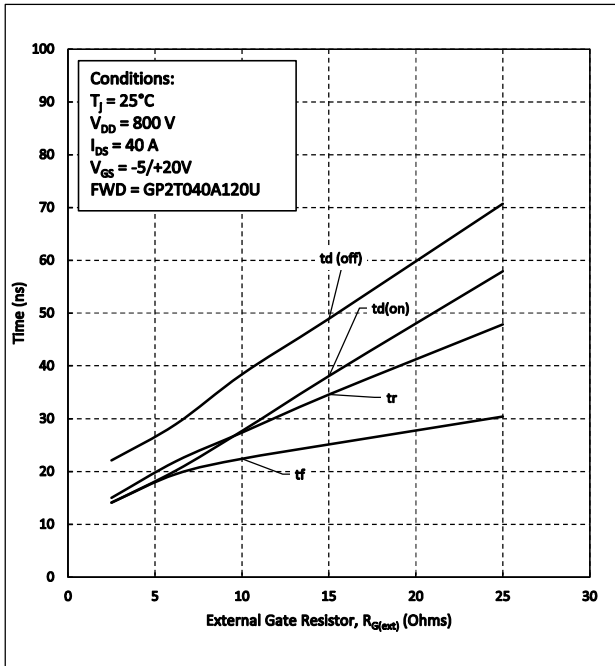


Figure 23. Switching Times vs $R_{G(\text{ext})}$

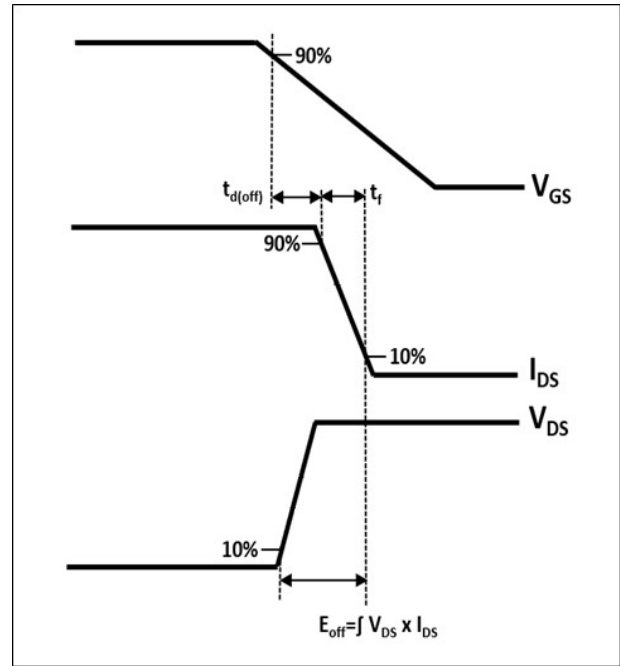


Figure 24. Turn-off Transient Definitions

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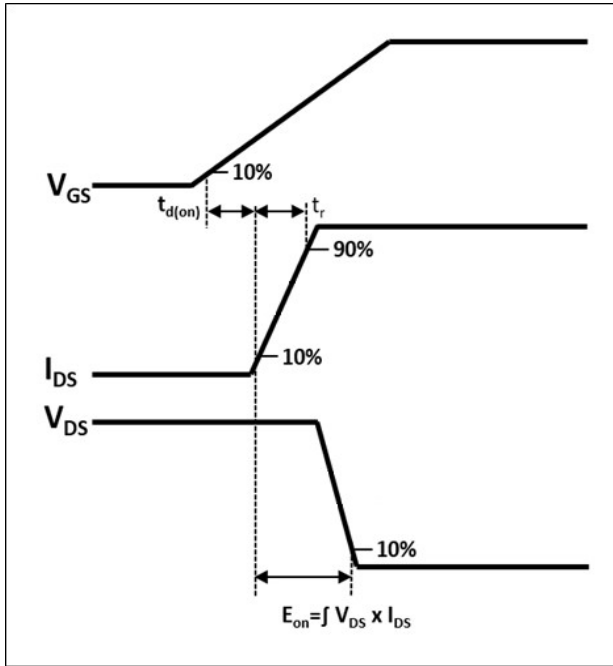


Figure 25. Turn-on Transient Definitions

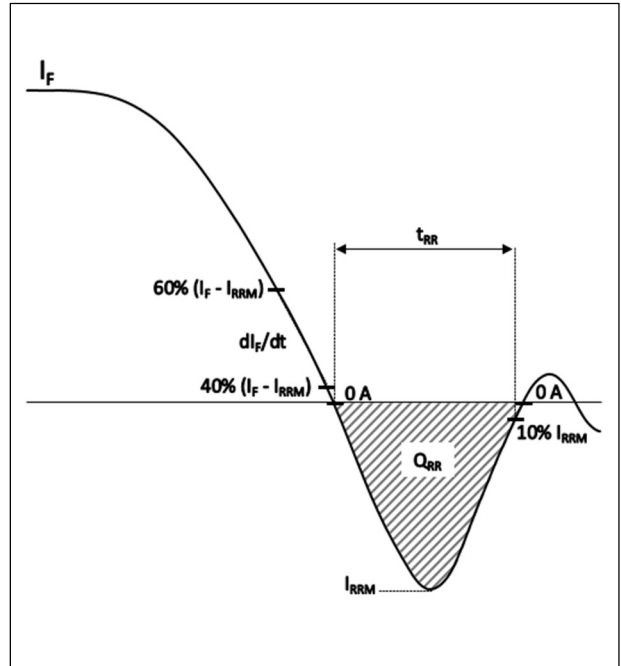
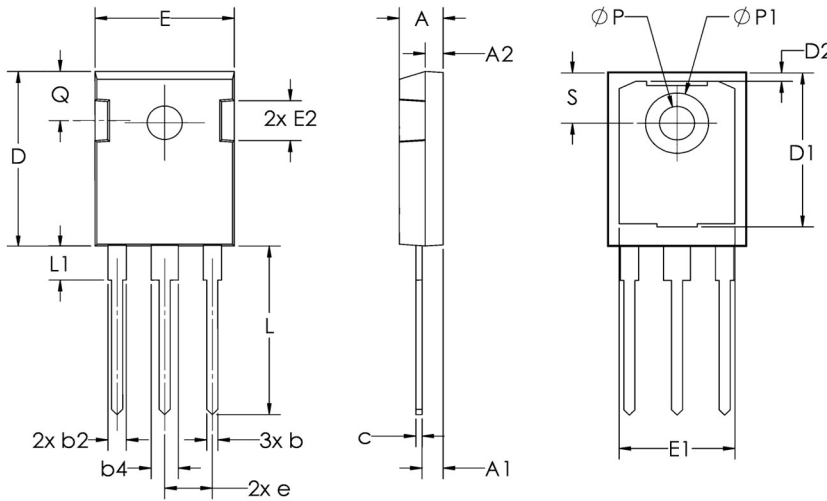


Figure 26. Reverse Recovery Definitions

Package Dimensions TO-247-3L



Sym	Millimeters		Inches	
	Min	Max	Min	Max
A	4.70	5.31	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.80	21.46	0.819	0.845
D1	13.08	17.65	0.515	0.695
D2	0.51	1.35	0.020	0.053
E	15.49	16.26	0.610	0.640
E1	13.46	14.16	0.530	0.557
E2	3.43	5.49	0.135	0.216
e	5.44 BSC		0.214 BSC	
L	19.81	20.32	0.780	0.800
L1	4.10	4.50	0.161	0.177
ØP	3.56	3.66	0.140	0.144
ØP1	7.06	7.39	0.278	0.291
Q	5.39	6.20	0.212	0.244
S	6.04	6.30	0.238	0.248